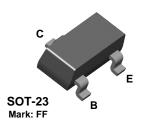


BCV27



NPN Darlington Transistor

This device is designed for applications requiring extremely high current gain at collector currents to 1.0 A. Sourced from Process 05.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	30	V
V _{CBO}	Collector-Base Voltage	40	V
V _{EBO}	Emitter-Base Voltage	10	V
I _C	Collector Current - Continuous	1.2	A
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		*BCV27	
P_D	Total Device Dissipation Derate above 25°C	350 2.8	mW mW/∘C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

^{*}Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

¹⁾ These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

NPN Darlington Transistor

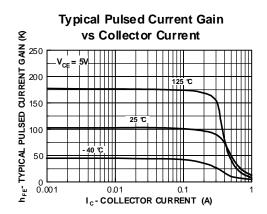
(continued)

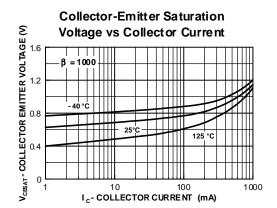
FI	lectri	ical	Cha	arac	cter	istics
_		vai	VIII	aı a ı	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	ISLICS

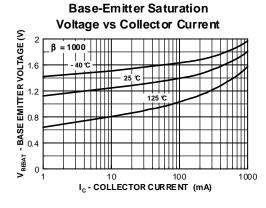
TA = 25°C unless otherwise noted

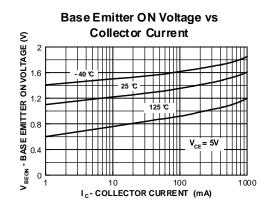
Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
OFF CHA	RACTERISTICS					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{ mA}, I_B = 0$	30			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	40			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 100 \text{ nA}, I_C = 0$	10			V
I _{CBO}	Collector-Cutoff Current	$V_{CB} = 30 \text{ V}, I_{E} = 0$			0.1	μΑ
I _{EBO}	Emitter-Cutoff Current	$V_{EB} = 10 \text{ V}, I_{C} = 0$			0.1	μΑ
ON CHAR	ACTERISTICS					
	ACTERISTICS DC Current Gain	$I_C = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$	4,000 10,000			
∩ _{FE}	DC Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$			1.0	V
h _{FE}	DC Current Gain Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 100 \text{ mA}, I_B = 0.1 \text{ mA}$	10,000		1.0	V
N_{FE} $V_{\text{CE(sat)}}$ $V_{\text{BE(sat)}}$	DC Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$	10,000		1.0	V
N_{FE} $V_{\text{CE(sat)}}$ $V_{\text{BE(sat)}}$	DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 100 \text{ mA}, I_B = 0.1 \text{ mA}$	10,000	220		

Typical Characteristics





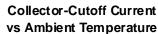


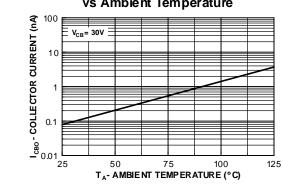


NPN Darlington Transistor

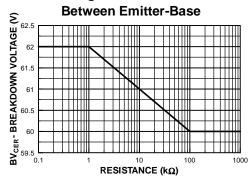
(continued)

Typical Characteristics (continued)

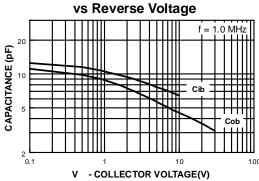




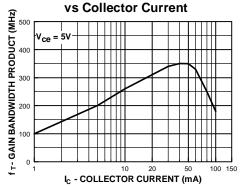
Collector-Emitter Breakdown Voltage with Resistance



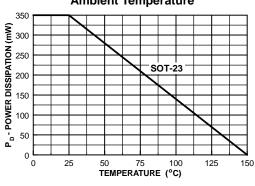
Input and Output Capacitance

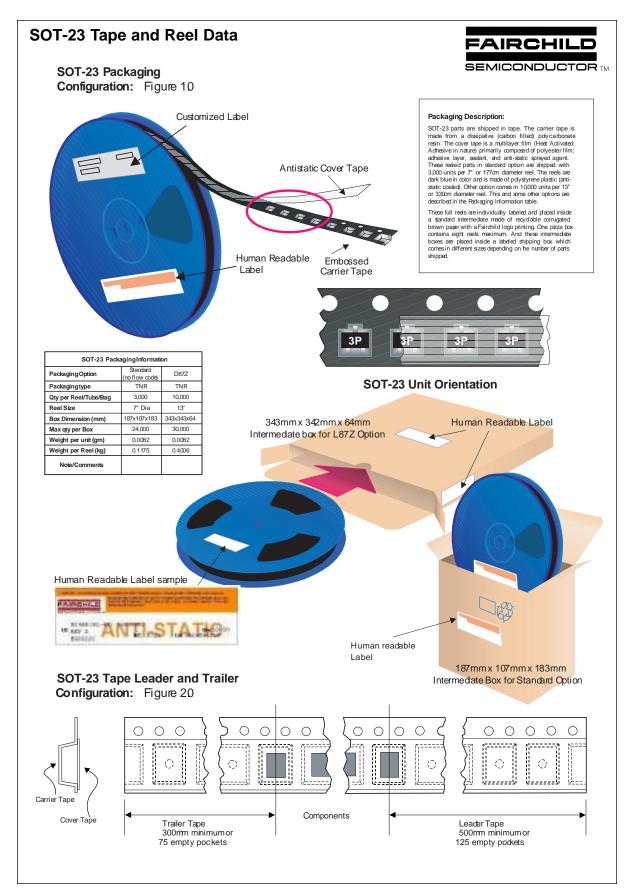


Gain Bandwidth Product



Power Dissipation vs Ambient Temperature

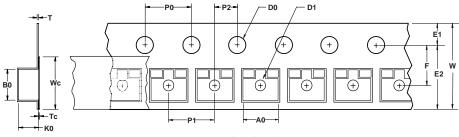




SOT-23 Tape and Reel Data, continued

SOT-23 Embossed Carrier Tape

Configuration: Figure 3.0



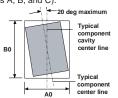
User Direction of Feed	

	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
SOT-23 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

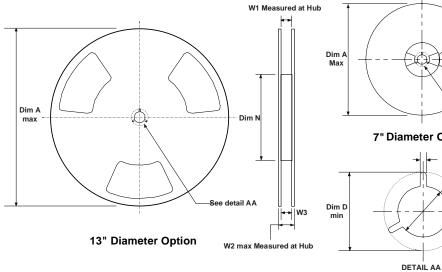


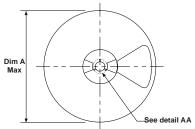
Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

SOT-23 Reel Configuration: Figure 4.0



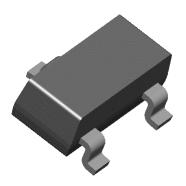


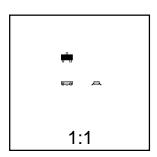
7" Diameter Option

Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9



SOT-23 (FS PKG Code 49)

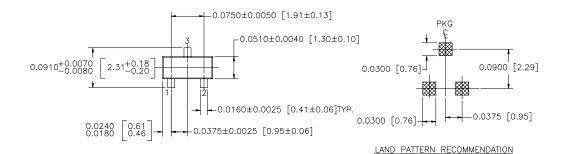


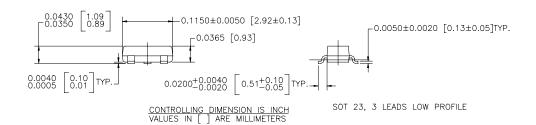


Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0082





NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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